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Microfabrication Techniques for Accelerators

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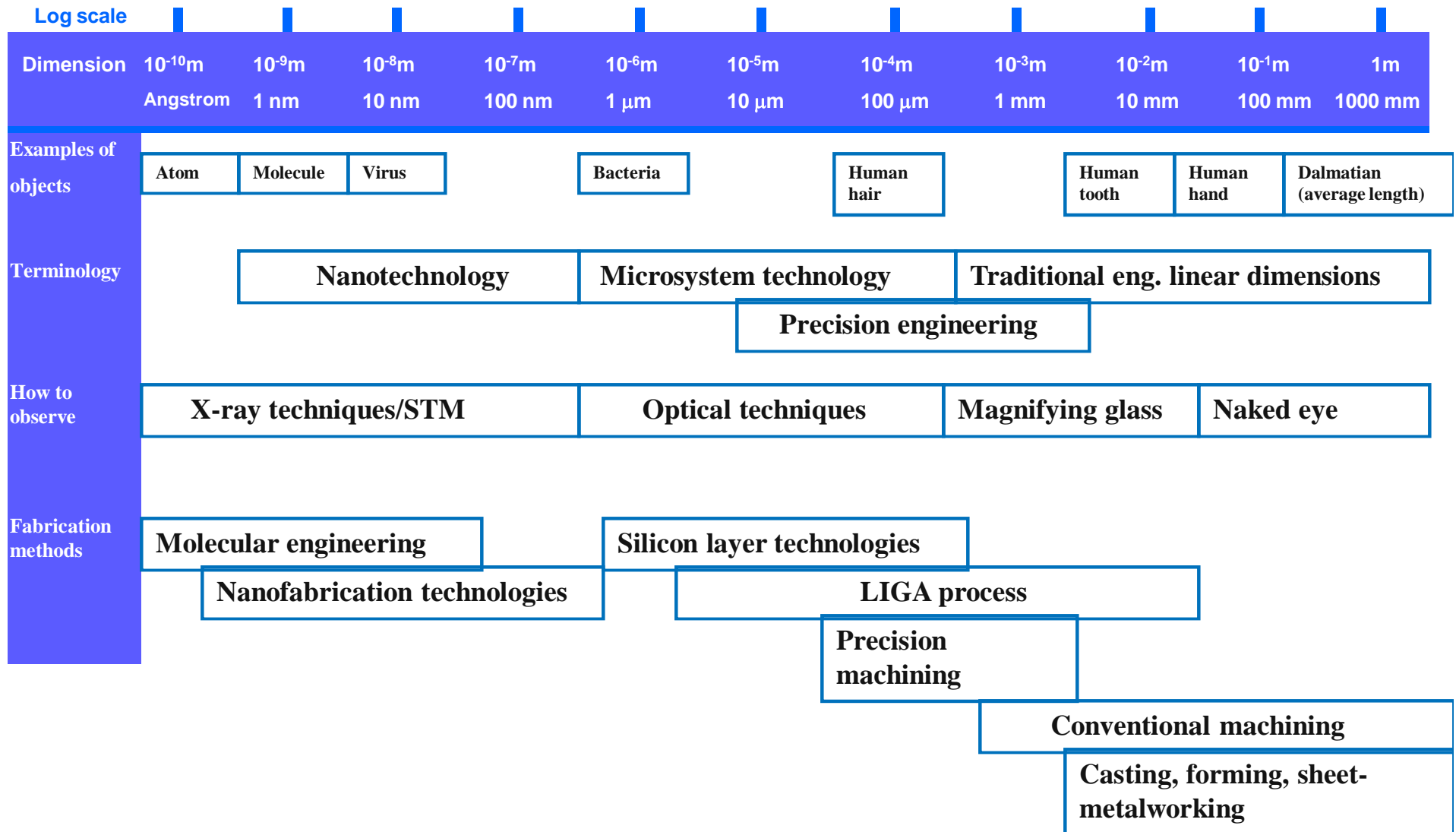
Symposium in Memory of Robert H. Siemann

and ICFA Mini-Workshop on Novel Concepts for Linear Accelerators and Colliders

Outline

- Terminology
- Microfabrication methods and tools
- DXRL at APS
- Summary

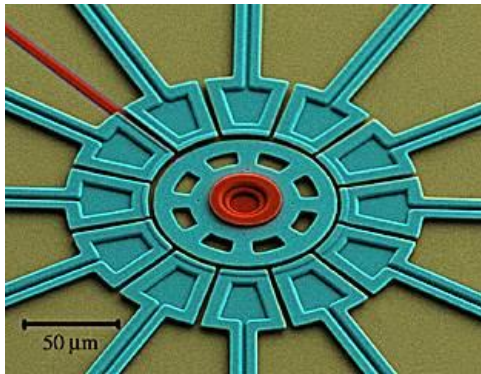
Terminology and relative sizes



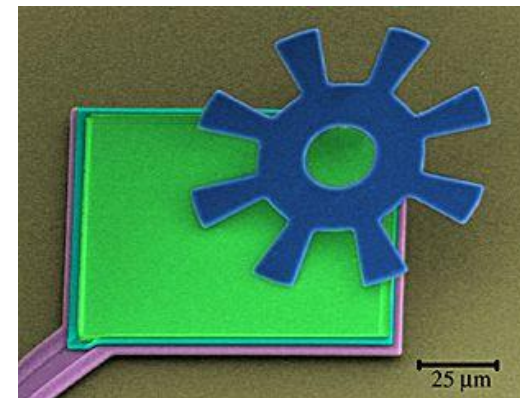
Microfabrication methods and tools - MEMS

Basic idea is to find a way to circumvent the limitations imposed by normal machining.

- MEMS (Micro-electrical-mechanical systems)
 - Fabricated at micron to millimeter sizes using a single silicon substrate
 - Used to fabricated sensors, motors, actuators, mirrors
 - *Wide range of industrial and consumer applications*
 - MEMS accelerometers for automobile airbag systems
 - MVED applications
 - *MEMS-based reflex klystron (JPL)*



A salient-pole electrostatic ally actuated micromotor made from polycrystalline silicon using surface micromachining techniques.



A mechanical gear which is smaller than a human hair

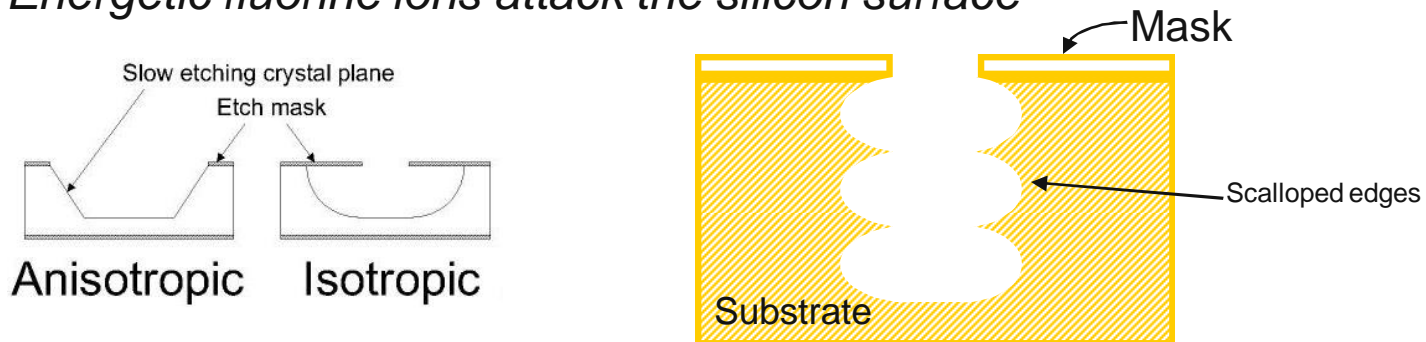
MEMS fabrication process

■ Wet Etching

- Isotropic wet etching uses solutions of hydrofluoric, nitric, and acetic acid, HNA.
- It produces hemispherical shaped cavities below the mask aperture.
- Lateral etch rate is about the same as vertical etch rate
- Anisotropic wet etching of silicon is done using either potassium hydroxide, KOH, or a solution of ethylene diamine and pyrocatechol, EDP

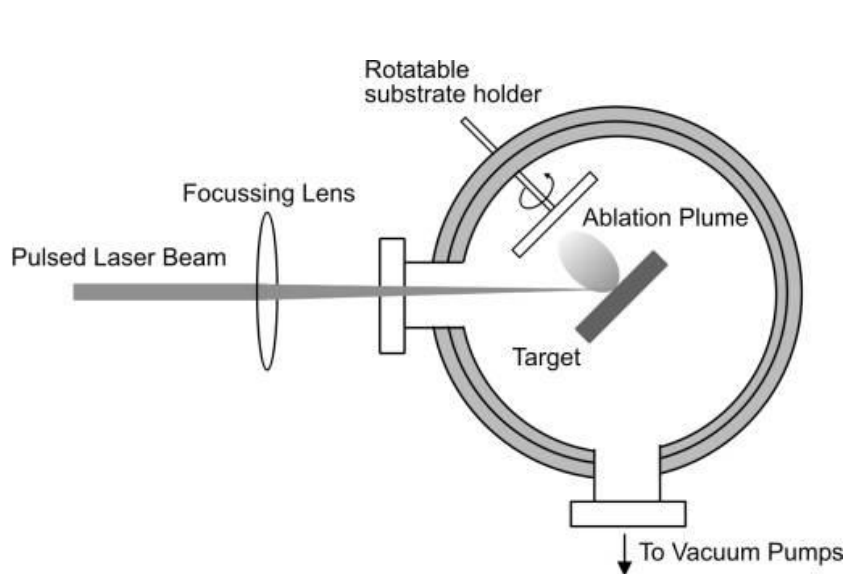
■ Dry Etching

- It provides a better control and faster etch rates than either isotropic or anisotropic wet etching.
- It refers to the process of reactive ion etching (RIE)
 - *Ionization of fluorine-rich reactive gas in a plasma chamber*
 - *Energetic fluorine ions attack the silicon surface*

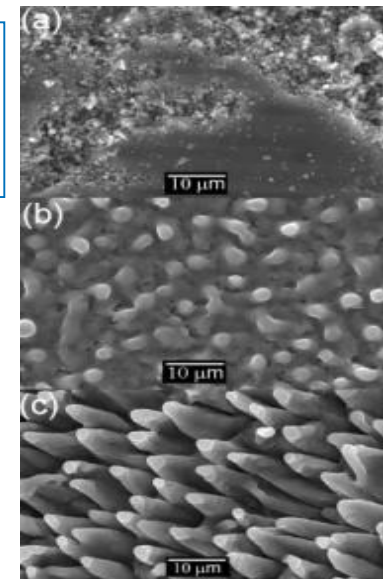


Microfabrication methods and tools – Laser Ablation

- Laser ablation micromachining uses the very high power density and very short pulse of the laser to vaporize the surface of a material without transferring heat to the surrounding area.
- It can be applied to a wide variety of materials including metals, ceramics, semiconductors and plastics.
 - The depth of the etch can only be done by knowing the material removal rate per pulse and counting pulses or by external measurement.



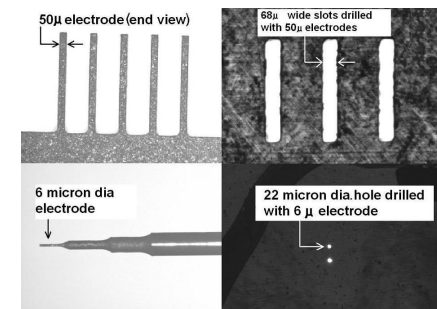
- a) Pre-ablation
- b) After ablation with one pulse
- c) After ablation with 10 pulses



SEM images of an MgB₂ ablated at 193 nm @12 J/cm²

Microfabrication methods and tools – EDM

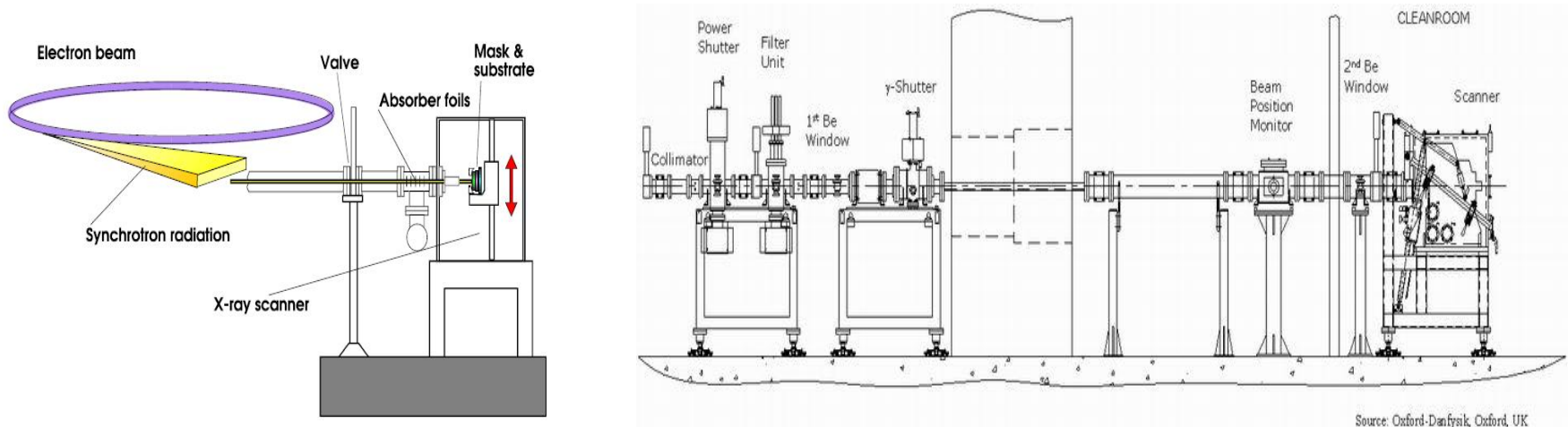
- Electric Discharge Machining uses large electric field arcs across the gap between the two metal surfaces.
- The arc raises the local surface temperature to between 8,000C and 12,000C and melts a roughly hemispherical volume on both the electrode and the work piece.
- Since the surface is formed by millions of small craters, it has a very poor surface finish.
- This can be improved considerably with finishing cuts, smaller wire diameter, lower electric fields.
- It needs additional treatment for low RF loss applications.
- Dimensional accuracy for EDM is roughly the same as precision machining.
- EDM gains in accuracy from its noncontact material removal, compared to normal machining.
- Disadvantage: variation in height of the crater-defined surface.
- New wire-handling and tensioning systems have allowed EDM wire diameters to ~ 20 μ m (as compared to 0.3 mm – 0.03 mm), μ EDM.



Slide courtesy: MicroBridge Services, Ltd

Microfabrication methods and tools – LIGA

- LIGA is a process in IC fabrication which involves lithography, electroplating, and molding on a given substrate. (Lithographie, Galvanoformung und Abformug)
- LIGA allows structures to have heights of over 100 μm with respect to the lateral size.
- LIGA fabricates High Aspect Ratio Structures (HARMS).
- The ratio between the height and the lateral size is the aspect ratio (e.g. 100:1)
- Ideal for fabrication of RF resonant cavities with frequencies from 30 GHz to 1 THz.
- Unlike semiconductor lithography, LIGA uses very thick resist films.

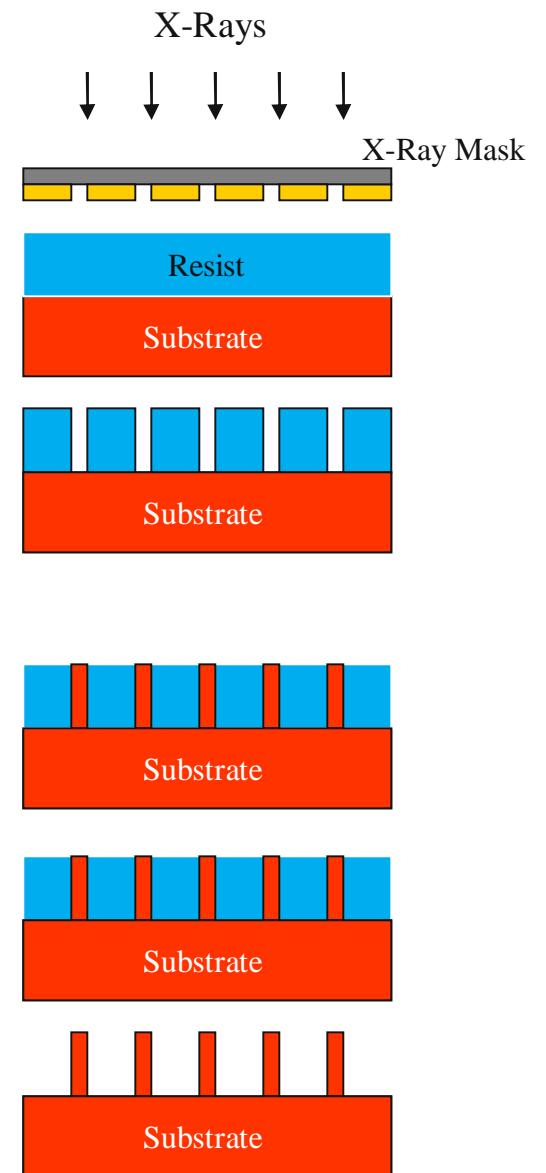


Deep X-ray Lithography and Electroforming

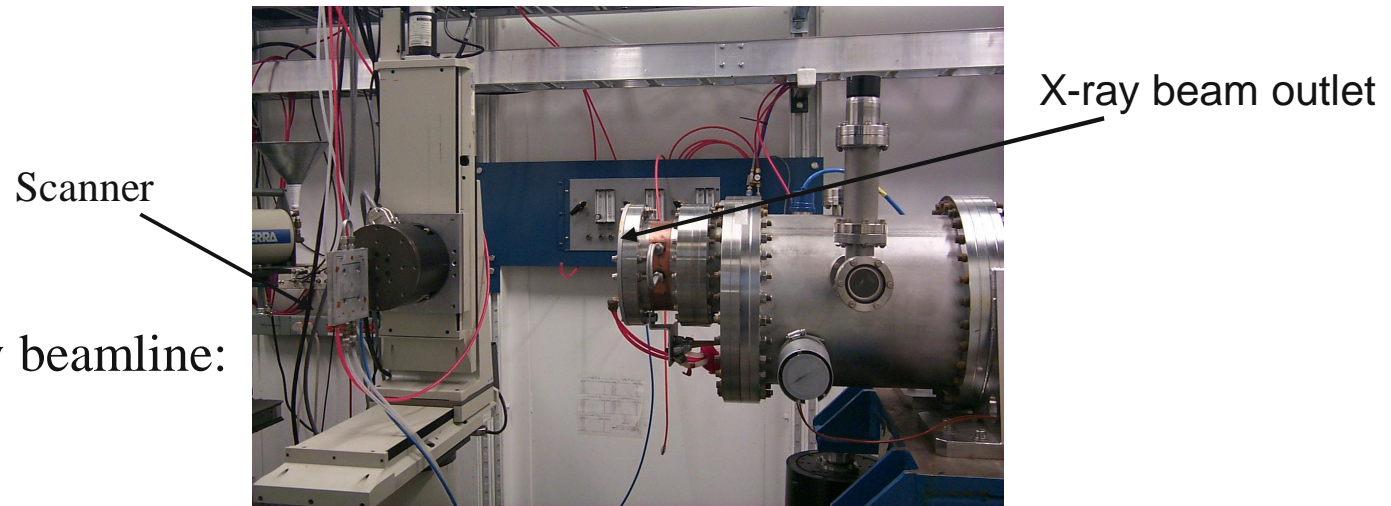
- Silicon wafer, 250- μm -thick
- Gold absorber, 45-60- μm -thick
- PMMA, 1 -3-mm-thick
- Copper base, 50-mm-thick
- Copper plating

■ SU-8 LIGA

- An alternative to PMMA
- For X-ray LIGA applications, it has a significant advantage:
 - *About 200 times more sensitive to X rays than PMMA*
 - *This drops exposure times by two orders of magnitude.*
 - *Disadvantage: The etchants that attack the exposed SU-8 also attack the metal surface of the LIGA part.*



X-ray Exposure Station at the Advanced Photon Source of Argonne National Laboratory



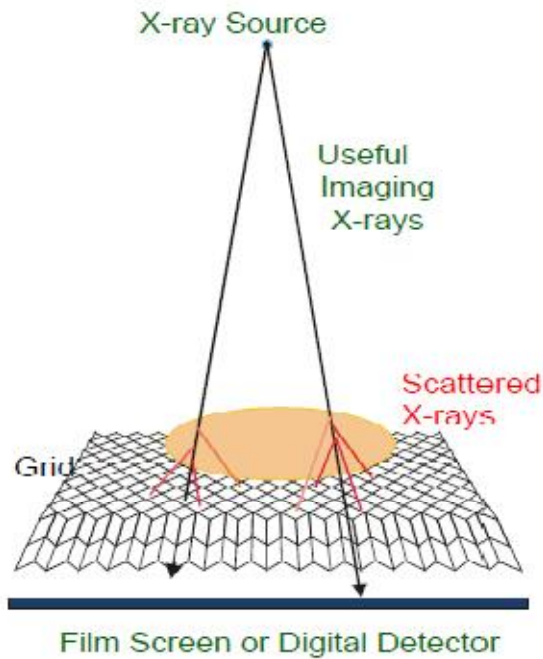
APS Lithography beamline:

- 19.5 keV
- Highly collimated beam (< 0.1 mrad)
- Beam size @exposure station: 100 (H) x 5 (v) mm²
- Using a high-speed scanner (100 mm/sec) for uniform exposure.
- Precision angular (~ 0.1 mrad) and positional (< 1 micron) control of the sample.
- exposure time:
 - 1-mm thick PMMA (100 x 25 mm²) $\sim 1/2$ hr
 - 10-mm thick PMMA ~ 2 -3 hrs

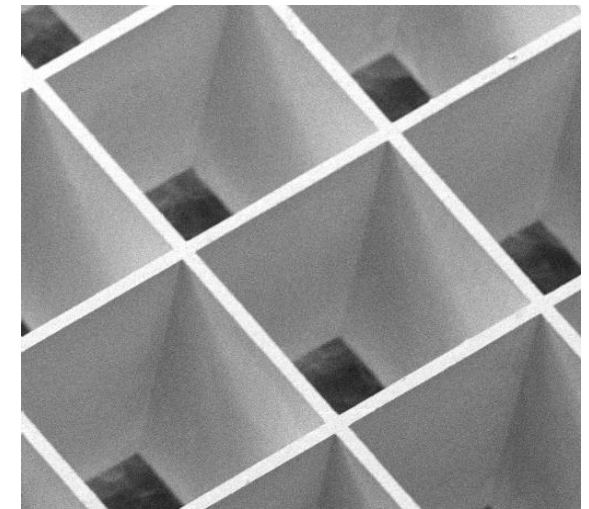
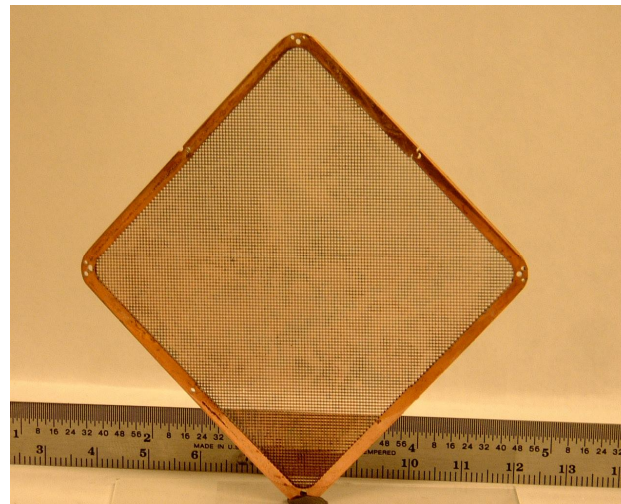
Antiscatter Grid for Mammography

■ Scatter

- Produces slowly varying background fog
- Reduces subject contrast
- Reduces the ability to identify diseased tissues



Detail of x-ray mask used for obtaining freestanding copper antiscatter grid

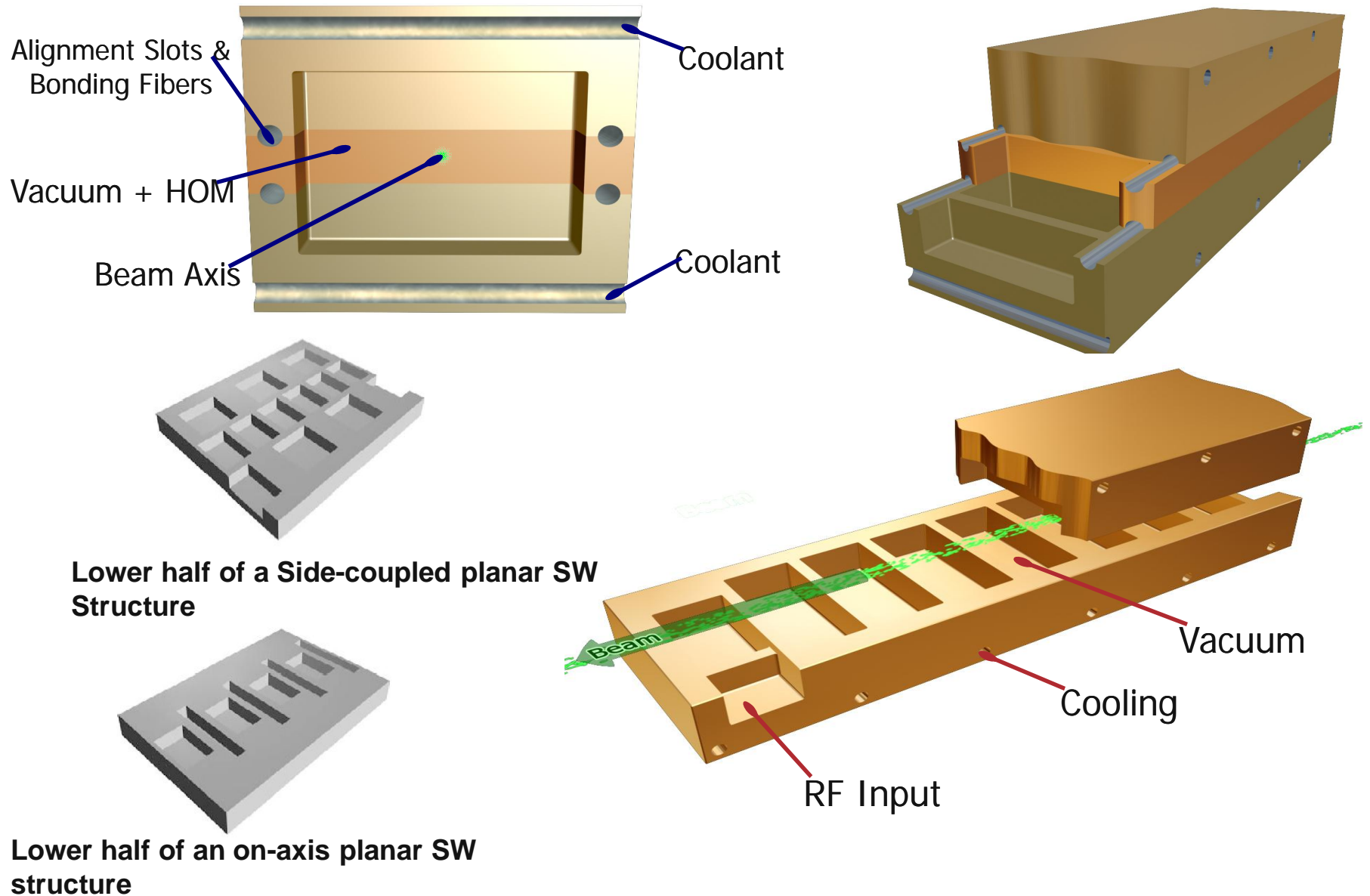


Freestanding focused to the point copper antiscatter grid 60 mm x 60 mm in size with 25- μ m-wide septa walls and 550 μ m period and 2.8 mm tall (grid ratio 5.3).

Unique benefits of ANL

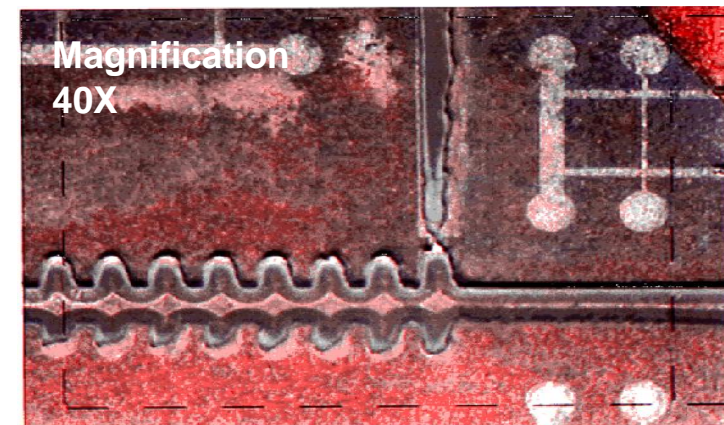
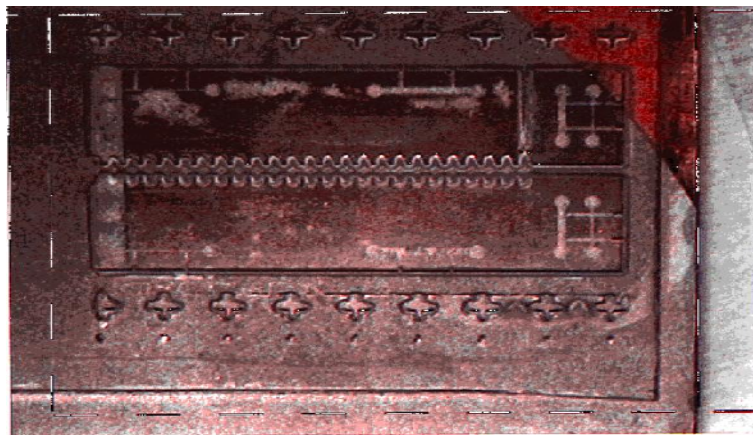
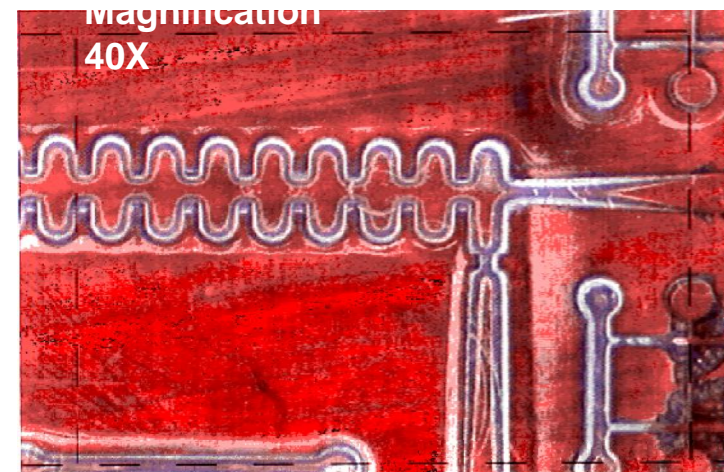
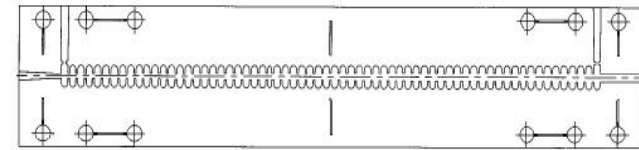
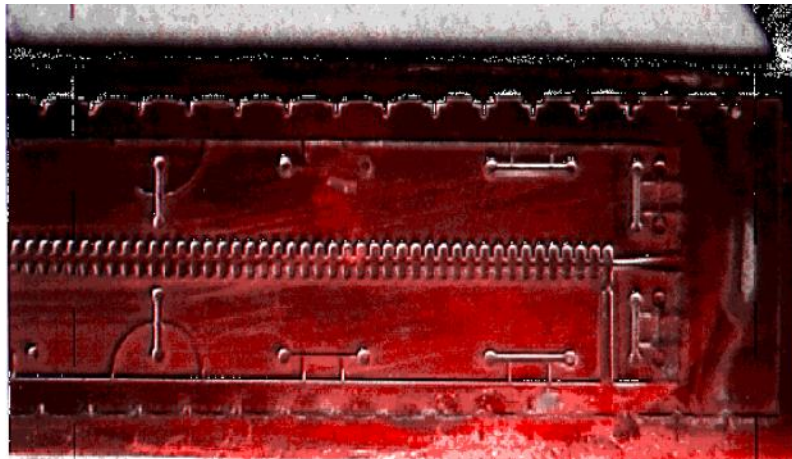
- APS is one of the very few light sources worldwide suitable for micromechanics with a unique possibility of dynamic exposure for very tall (1-3mm) structures.
- Knowledgeable and experienced staff provides excellent user support.
- X-ray lithography station in Sector 10 is fully operational on a shared bend magnet beamline.
- Long experience in fabricating copper high-aspect ratio microstructures.

3-D Conceptual Planar Structure



PMMA Masks with DXRL: 94 GHz CG ¹

- Long structure (66 cells)

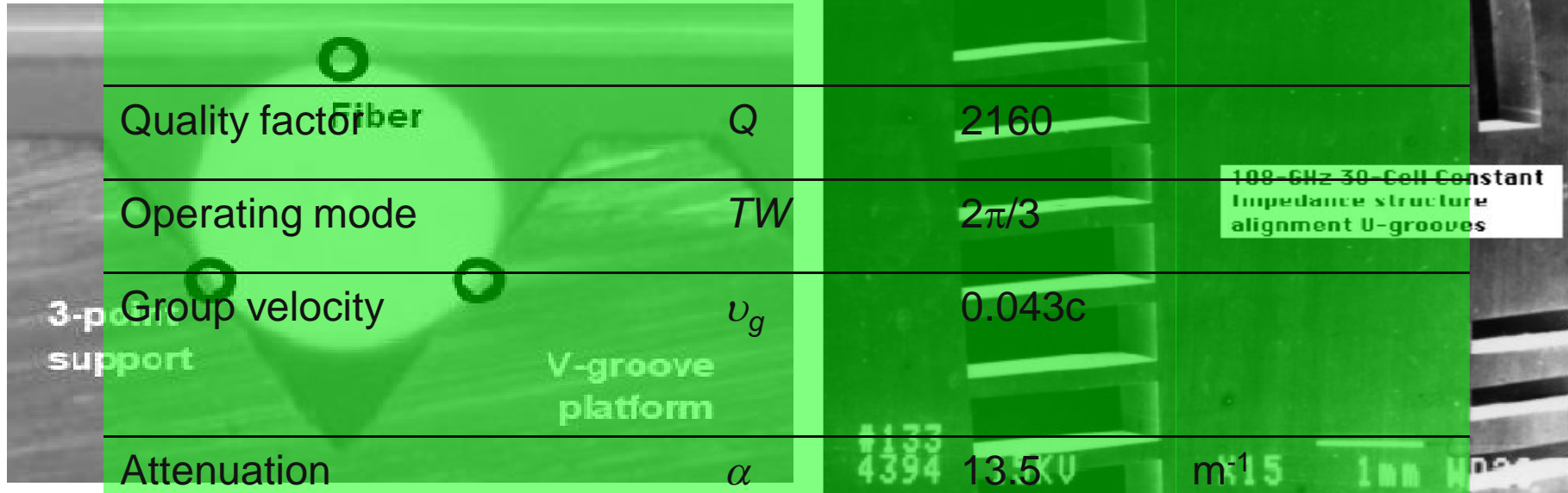


¹ J. Song, et al., Proc. Particle Accel Conf., Vancouver, B.C., Canada, 1997

Constant impedance cavity¹

- Muffin-tin cavity RF parameters
- High aspect ratio
- Surface roughness < 50 nm
- Frequency
- High accuracy < 1 μm

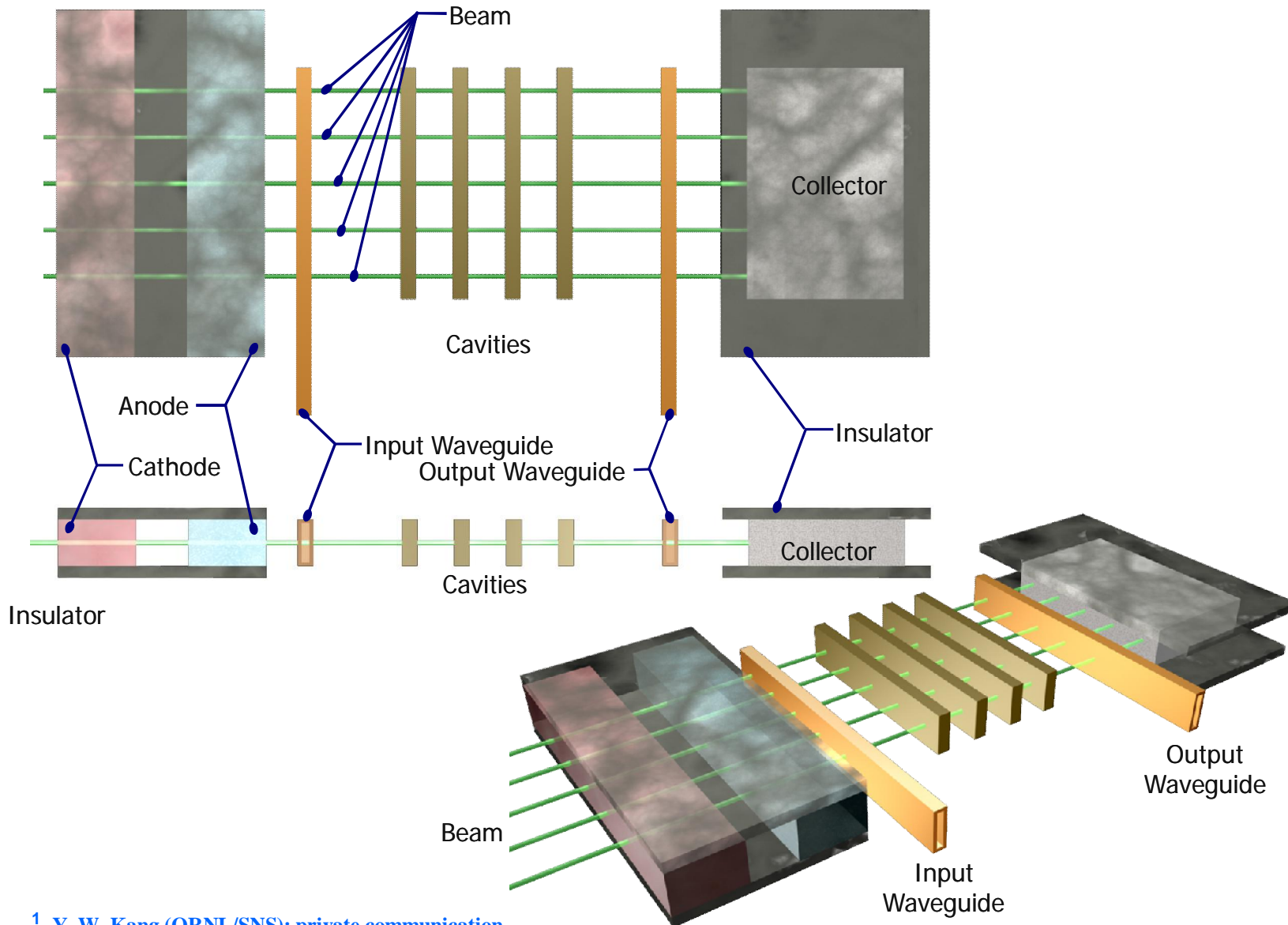
Frequency	f	120	GHz
Shunt impedance	R_0	312	MΩ/m
Quality factor	Q	2160	
Operating mode	TW	$2\pi/3$	
Group velocity	v_g	0.043c	
Attenuation	α		
Accel. Gradient	E	10	MV/m
Peak power	P	30	kW



SEM image of 108-GHz structure.

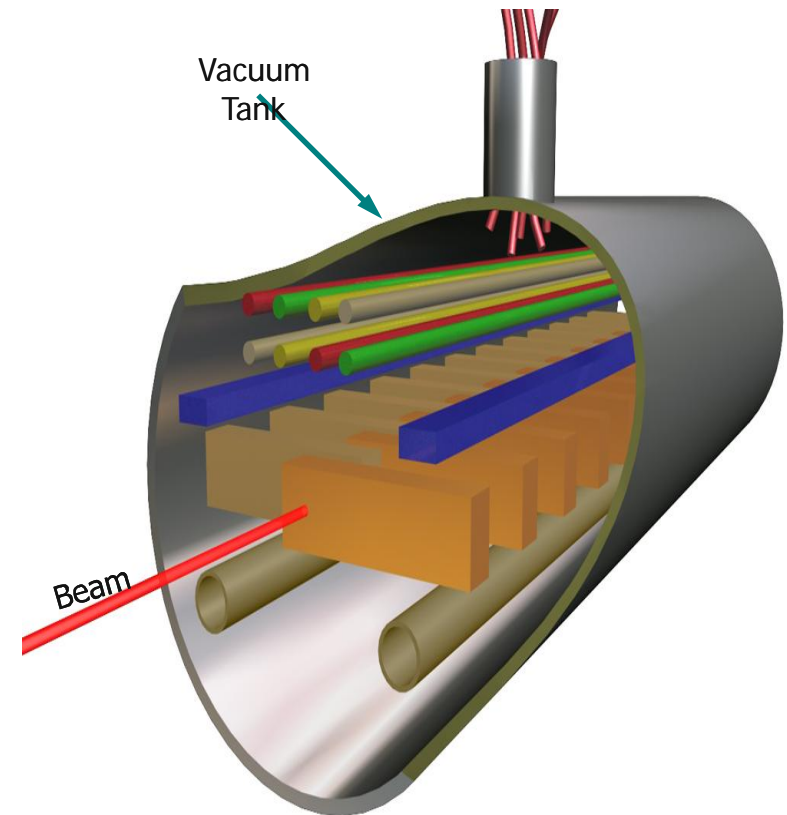
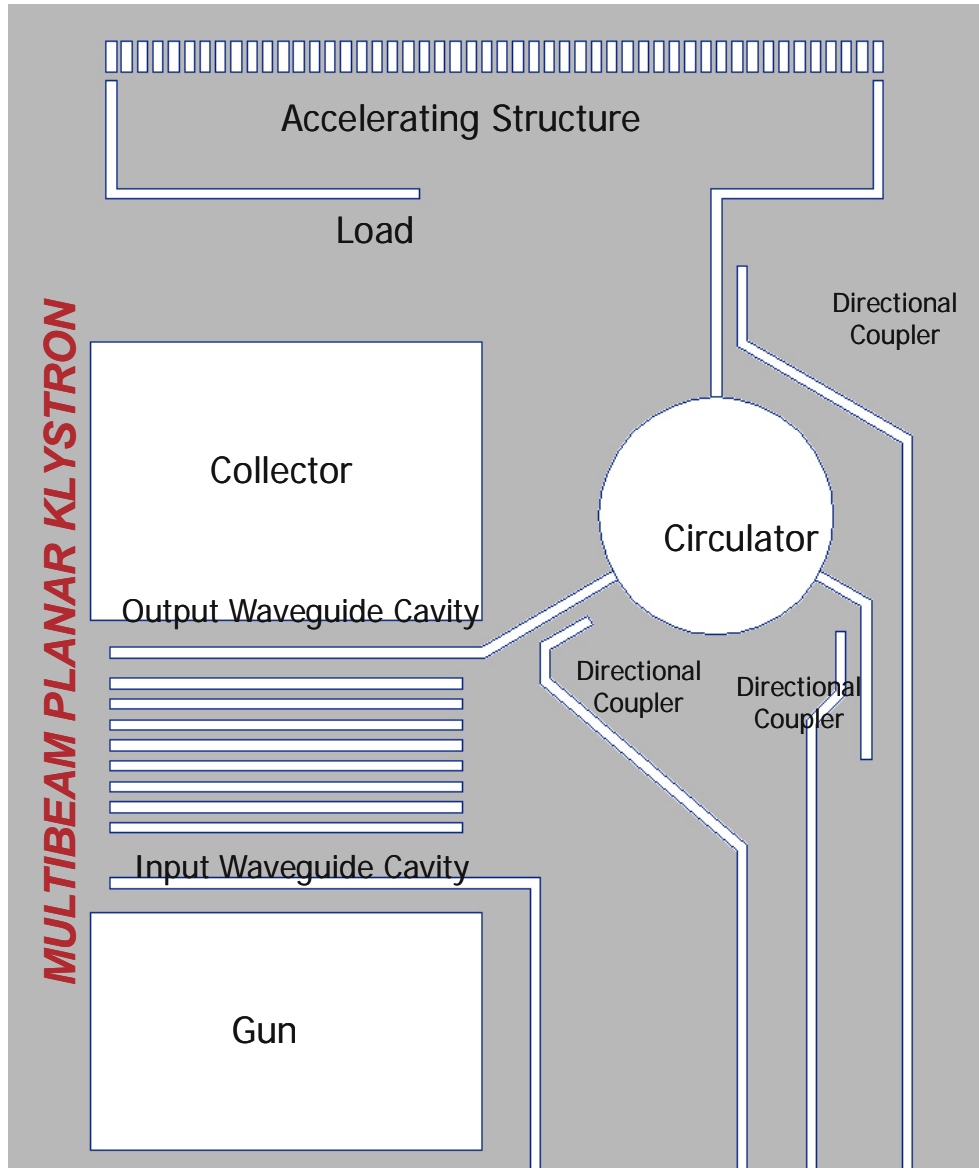
¹A. Nassiri, et al., Proc. Int. Electron Devices Meeting, Washington, DC, December 1993

Multi-beam Planar Klystron¹



¹ Y. W. Kang (ORNL/SNS): private communication

Accelerator on a Substrate



Comparison of Microfabrication Methods for RF Structures

- Each fabrication method discussed has specific advantages for different materials and geometries.
- Normal machining can produce RF structures up to several hundred gigahertz as long as surface finish and consequent surface losses are not important.
- In resonant structures where surface losses drastically degrade the performance, normal machining is limited to less than 100-GHz structures.
- EDM has similar issues regarding surface losses
 - Can handle hard-to-machine materials. Only conductive materials
- LIGA is effective in a range of frequency defined by
 - Depth to which the photoresist can be exposed
 - *6-mm thick PMMA “routine”*
 - *10-mm thick PMMA soon*
 - Dimensional accuracy limits of the mask and the diffraction of the light source.
 - *Smallest lateral size is 0.2 μm .*
 - *Aspect ratios can range up to 500.*
 - *Surface roughness is small (~ 30 nm).*

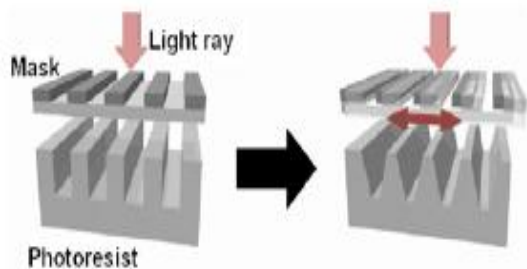
$$f \geq 25 \text{ GHz}$$

Characteristics of Microfabrication Methods

	Dimensional Accuracy (μm)	Surface Finish (nm)	Compatible Materials	Litho or Serial Process	Cost per Part	Frequency Range (GHz)
LIGA PMMA	±1	< 200	Metals	Litho	Low	25 - 600
LIGA SU-8	±1	< 200	Metals	Litho	Low	25 - 600
MEMS(WE)	±0.5	< 50	Silicon	Litho	Low	300-3000
MEMS (DRIE)	±0.5	< 50	Silicon	Litho	Low	300-3000
Laser ablation	±2	200-500	Almost any materials	Litho/Serial	High	100-300
EDM	±2	<1000	Conductors	Serial	High	0-300
Normal machining	±8	<1000	Almost any materials	Serial	Medium/High	0-100

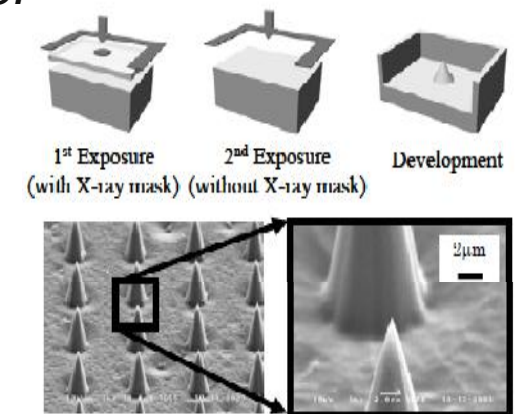
Can a “true” 3D structure be realized?

- As attractive DXRL is, it can only fabricate microstructures with vertical wall, which limits their application.
- Although 3D structures can be realized by various LIGA techniques, structures have walls parallel to the incident X-ray.
- To overcome these limitations with the conventional lithography techniques, Two recently new techniques have been developed:
 - A moving mask deep X-ray lithography (M²DXL)¹.
 - *M²DXL is a technique to fabricate microstructures with controllable inclined or curve wall.*
 - A double X-ray exposure technique²
 - *3D is realized by controlling the propagation direction of the PMMA dissolution front. This is achieved by irradiating the whole PMMA surface again without the X-ray mask after the first exposure.*



Method	Conventional	Moving Mask	
Mask Pattern	L/S = 50 μm	L/S = 50 μm	Hole (ø20 μm) / Dot (ø50 μm)
Mask Movement	-	20 μm	ø 25 μm / ø 25 μm
Deposited Dose Profile			
SEM			

3D microstructure fabricated by moving mask UV lithography techniques.



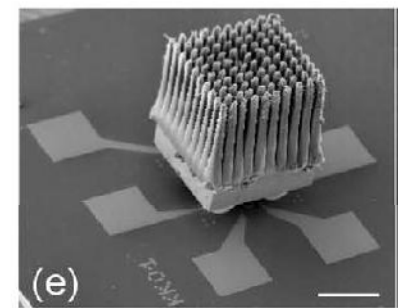
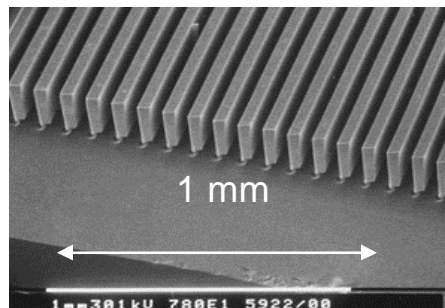
¹ Y. Hirai, et. al, J. Micromech. 17 (2007)

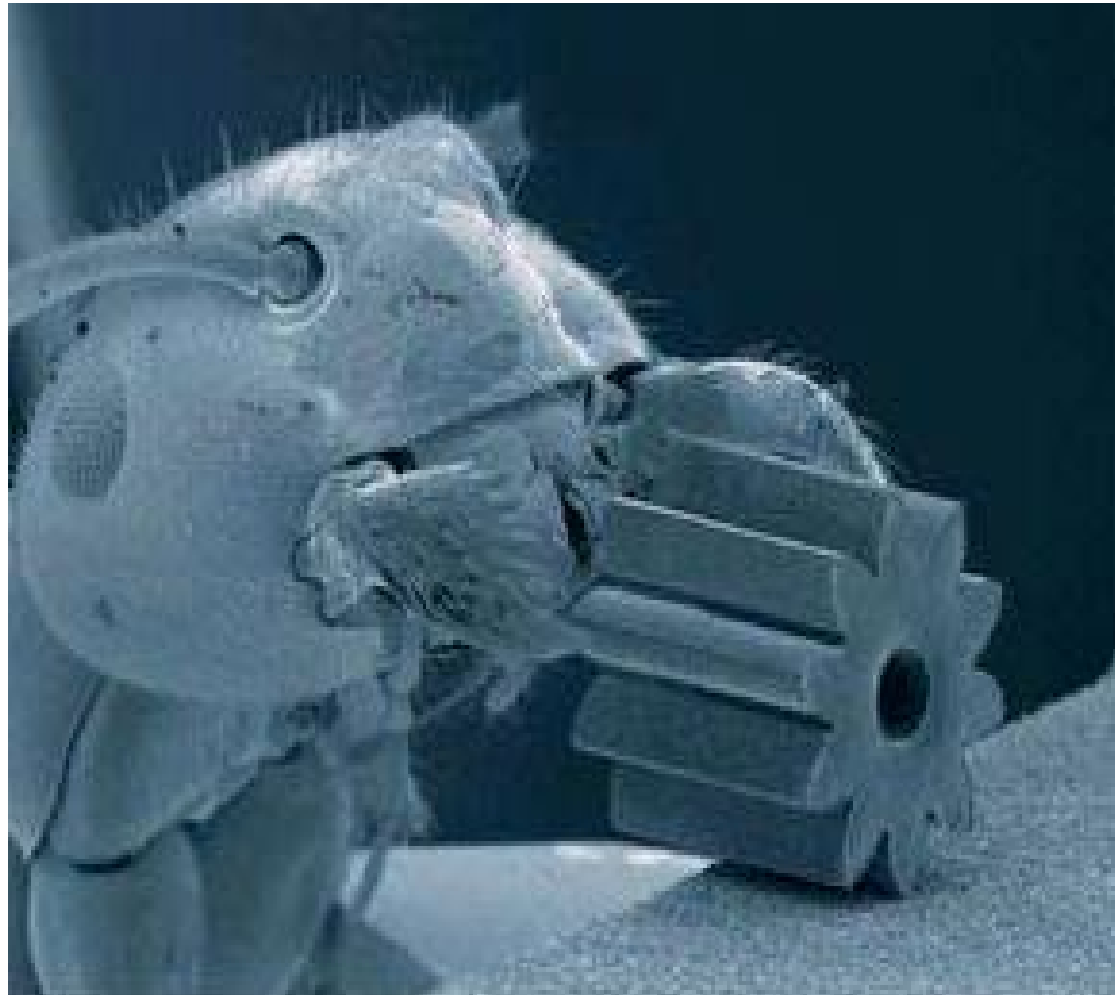
² N. Matsuzuka, et. al, 17th IEEE MEMS, 2004

Summary

- Technology for a fully integrated design is not (yet) available and not likely in the near future.
- Hybrid design, ala hybrid integrated-electronic circuits, is closer to being available, requires considerable R&D.
- Fabrication challenges of RF structures and circuits
 - Vacuum-sealing and vacuum pumping of circuit with sub-millimeter beam apertures
 - RF losses due to surface roughness
 - $\delta = 200 \text{ nm}$ @95 GHz and 66 nm @1 THz for copper
 - Need surface roughness less than the skin depth
 - Dimensional accuracy of cavities/circuits and alignment
 - Dimensional accuracy required $\propto 1/BW$
 - Beam transport and magnetic focusing
 - Heat transfer and structure cooling (microchannel/ nanotubes)
 - CW and pulse heating

Microchannel array
formed by silicon
DRIE





Thank you.